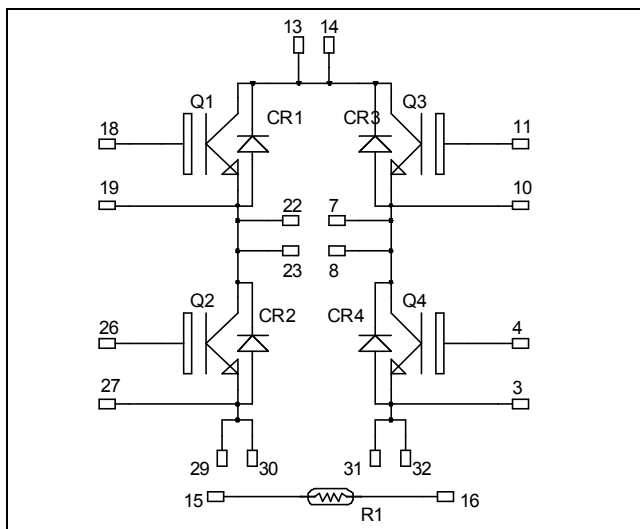


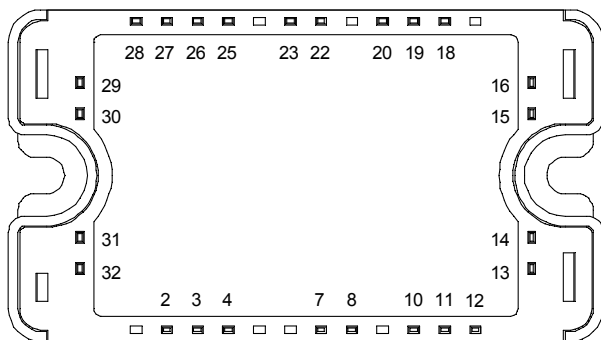
**Full - Bridge
NPT & Trench + Field Stop® IGBT
Power module**

Trench & Field Stop® IGBT Q1, Q3:
 $V_{CES} = 600V$; $I_C = 30A$ @ $T_c = 80^\circ C$

Fast NPT IGBT Q2, Q4:
 $V_{CES} = 600V$; $I_C = 30A$ @ $T_c = 80^\circ C$



Top switches : Trench + Field Stop IGBT®
Bottom switches : FAST NPT IGBT



All multiple inputs and outputs must be shorted together
13/14 ; 15/16 ; 26/27 ; 31/32

Application

- Solar converter

Features

- **Q2, Q4 FAST Non Punch Through (NPT) IGBT**
 - Switching frequency up to 100 kHz
 - RBSOA & SCSOA rated
 - Low tail current
- **Q1, Q3 Trench & Field Stop IGBT®**
 - Low voltage drop
 - Switching frequency up to 20 kHz
 - RBSOA & SCSOA rated
 - Low tail current

- Kelvin emitter for easy drive
- Very low stray inductance
- High level of integration
- Internal thermistor for temperature monitoring

Benefits

- Optimized conduction & switching losses
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- Easy paralleling due to positive T_c of V_{CESat}
- RoHS Compliant



CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

All ratings @ $T_j = 25^\circ\text{C}$ unless otherwise specified

1. Top switches

1.1 Top Trench + Field Stop IGBT® characteristics

Absolute maximum ratings

Symbol	Parameter	Max ratings	Unit
V_{CES}	Collector - Emitter Breakdown Voltage	600	V
I_C	Continuous Collector Current	$T_C = 25^\circ\text{C}$ 50	A
		$T_C = 80^\circ\text{C}$ 30	
I_{CM}	Pulsed Collector Current	$T_C = 25^\circ\text{C}$ 60	
V_{GE}	Gate – Emitter Voltage	± 20	V
P_D	Maximum Power Dissipation	$T_C = 25^\circ\text{C}$ 90	W
RBSOA	Reverse Bias Safe Operating Area	$T_j = 150^\circ\text{C}$ 60A @ 550V	

Electrical Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
I_{CES}	Zero Gate Voltage Collector Current	$V_{GE} = 0\text{V}, V_{CE} = 600\text{V}$			250	μA
$V_{CE(sat)}$	Collector Emitter Saturation Voltage	$V_{GE} = 15\text{V}$ $I_C = 30\text{A}$ $T_j = 25^\circ\text{C}$		1.5	1.9	V
		$T_j = 150^\circ\text{C}$		1.7		
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}, I_C = 400\mu\text{A}$	5.0	5.8	6.5	V
I_{GES}	Gate – Emitter Leakage Current	$V_{GE} = 20\text{V}, V_{CE} = 0\text{V}$			300	nA

Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
C_{ies}	Input Capacitance	$V_{GE} = 0\text{V}$ $V_{CE} = 25\text{V}$ $f = 1\text{MHz}$		1600		pF
C_{oes}	Output Capacitance			110		
C_{res}	Reverse Transfer Capacitance			50		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (25°C) $V_{GE} = \pm 15\text{V}$ $V_{Bus} = 300\text{V}$ $I_C = 30\text{A}$ $R_G = 10\Omega$		110		ns
T_r	Rise Time			45		
$T_{d(off)}$	Turn-off Delay Time			200		
T_f	Fall Time			40		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (150°C) $V_{GE} = \pm 15\text{V}$ $V_{Bus} = 300\text{V}$ $I_C = 30\text{A}$ $R_G = 10\Omega$		120		ns
T_r	Rise Time			50		
$T_{d(off)}$	Turn-off Delay Time			250		
T_f	Fall Time			60		
E_{on}	Turn-on Switching Energy	$V_{GE} = \pm 15\text{V}$ $V_{Bus} = 300\text{V}$ $I_C = 30\text{A}$ $R_G = 10\Omega$ $T_j = 25^\circ\text{C}$		0.16		mJ
		$T_j = 150^\circ\text{C}$		0.3		
E_{off}	Turn-off Switching Energy	$T_j = 25^\circ\text{C}$		0.7		mJ
		$T_j = 150^\circ\text{C}$		1.05		
R_{thJC}	Junction to Case Thermal resistance				1.6	$^\circ\text{C/W}$

1.2 Top fast diode characteristics

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
V_{RRM}	Maximum Peak Repetitive Reverse Voltage			600			V
I_{RM}	Maximum Reverse Leakage Current	$V_R = 600V$	$T_j = 25^\circ C$			25	μA
			$T_j = 125^\circ C$			500	
I_F	DC Forward Current		$T_c = 80^\circ C$		25		A
V_F	Diode Forward Voltage	$I_F = 25A$			1.8	2.2	V
		$I_F = 50A$			2.2		
		$I_F = 25A$	$T_j = 125^\circ C$		1.6		
t_{rr}	Reverse Recovery Time	$I_F = 25A$ $V_R = 400V$ $di/dt = 200A/\mu s$	$T_j = 25^\circ C$		30		ns
			$T_j = 125^\circ C$		175		
Q_{rr}	Reverse Recovery Charge		$T_j = 25^\circ C$		55		nC
			$T_j = 125^\circ C$		485		
R_{thJC}	Junction to Case Thermal resistance					1.4	$^\circ C/W$

2. Bottom switches

2.1 Bottom Fast NPT IGBT characteristics

Absolute maximum ratings

Symbol	Parameter	Max ratings		Unit
V_{CES}	Collector - Emitter Breakdown Voltage	600		V
I_C	Continuous Collector Current	$T_C = 25^\circ C$	42	A
		$T_C = 80^\circ C$	30	
I_{CM}	Pulsed Collector Current	$T_C = 25^\circ C$	100	
V_{GE}	Gate – Emitter Voltage	± 20		V
P_D	Maximum Power Dissipation	$T_C = 25^\circ C$	140	W
RBSOA	Reverse Bias Safe Operating Area	$T_j = 125^\circ C$	60A@500V	

Electrical Characteristics

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
I_{CES}	Zero Gate Voltage Collector Current	$V_{GE} = 0V$ $V_{CE} = 600V$	$T_j = 25^\circ C$			250	μA
			$T_j = 125^\circ C$			500	
$V_{CE(sat)}$	Collector Emitter saturation Voltage	$V_{GE} = 15V$ $I_C = 30A$	$T_j = 25^\circ C$	1.7	2.0	2.45	V
			$T_j = 125^\circ C$		2.2		
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE3}, I_C = 1mA$		4		6	V
I_{GES}	Gate – Emitter Leakage Current	$V_{GE} = 20V, V_{CE} = 0V$				400	nA

Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
C _{ies}	Input Capacitance	V _{GE} = 0V		1350		pF
C _{oes}	Output Capacitance	V _{CE} = 25V		193		
C _{res}	Reverse Transfer Capacitance	f = 1MHz		120		
Q _g	Total gate Charge	V _{GE} = 15V		99		nC
Q _{ge}	Gate – Emitter Charge	V _{Bus} = 300V		10		
Q _{gc}	Gate – Collector Charge	I _C = 30A		60		
T _{d(on)}	Turn-on Delay Time	Inductive Switching (25°C)		30		ns
T _r	Rise Time	V _{GE} = 15V		12		
T _{d(off)}	Turn-off Delay Time	V _{Bus} = 400V		80		
T _f	Fall Time	I _C = 30A R _G = 6.8Ω		15		
T _{d(on)}	Turn-on Delay Time	Inductive Switching (125°C)		32		ns
T _r	Rise Time	V _{GE} = 15V		12		
T _{d(off)}	Turn-off Delay Time	V _{Bus} = 400V		90		
T _f	Fall Time	I _C = 30A R _G = 6.8Ω		21		
E _{on}	Turn-on Switching Energy	V _{GE} = 15V V _{Bus} = 400V I _C = 30A R _G = 6.8Ω	T _j = 125°C	0.3		mJ
E _{off}	Turn-off Switching Energy		T _j = 125°C	0.8		
R _{thJC}	Junction to Case Thermal resistance				0.9	°C/W

2.2 Bottom diode characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
V _{RRM}	Maximum Peak Repetitive Reverse Voltage		600			V
I _{RM}	Maximum Reverse Leakage Current	V _R = 600V	T _j = 25°C		150	μA
			T _j = 125°C		500	
I _F	DC Forward Current		T _c = 80°C	15		A
V _F	Diode Forward Voltage	I _F = 15A		1.6	1.8	V
		I _F = 30A		1.9		
		I _F = 15A	T _j = 125°C	1.4		
t _{rr}	Reverse Recovery Time	I _F = 15A V _R = 400V	T _j = 25°C	40		ns
		di/dt = 200A/μs	T _j = 125°C	150		
Q _{rr}	Reverse Recovery Charge		T _j = 25°C	95		nC
			T _j = 125°C	520		
R _{thJC}	Junction to Case Thermal resistance				2.0	°C/W

3. Temperature sensor

NTC (see application note APT0406 on www.microsemi.com for more information).

Symbol	Characteristic	Min	Typ	Max	Unit
R ₂₅	Resistance @ 25°C		50		kΩ
B _{25/85}	T ₂₅ = 298.15 K		3952		K

$$R_T = \frac{R_{25}}{\exp \left[B_{25/85} \left(\frac{1}{T_{25}} - \frac{1}{T} \right) \right]}$$

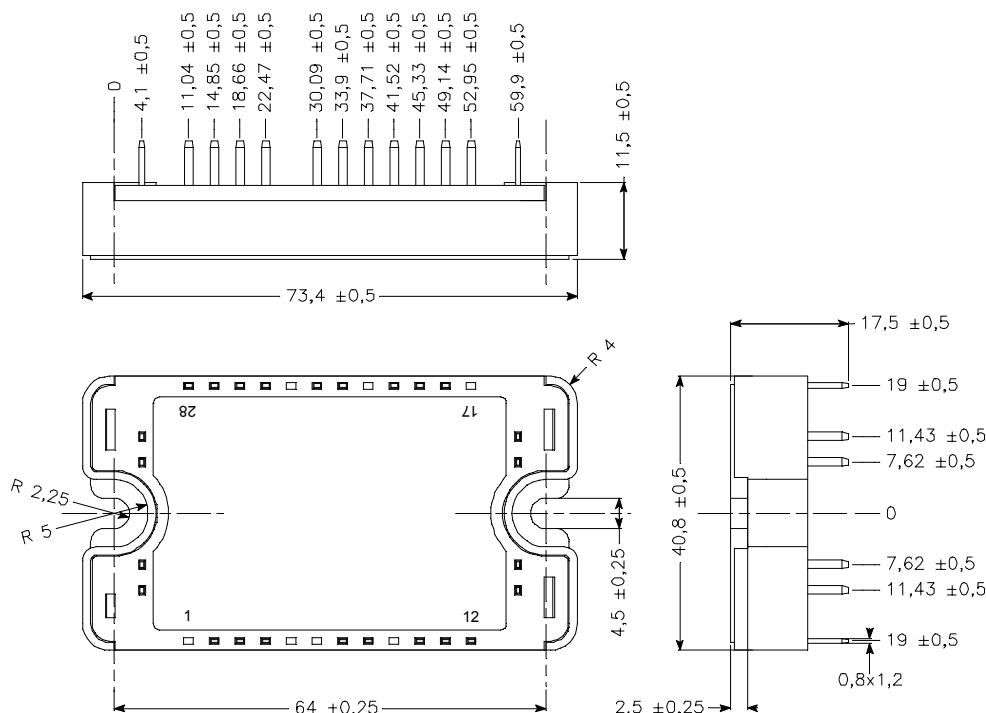
T: Thermistor temperature
R_T: Thermistor value at T

4. Package characteristics

Symbol	Characteristic			Min	Typ	Max	Unit
V _{ISOL}	RMS Isolation Voltage, any terminal to case t=1 min, I isol<1mA, 50/60Hz			2500			V
T _J	Operating junction temperature range			-40		150*	°C
T _{STG}	Storage Temperature Range			-40		125	
T _C	Operating Case Temperature			-40		100	
Torque	Mounting torque	To heatsink	M4	2.5		4.7	N.m
Wt	Package Weight					110	g

$T_J=175^{\circ}C$ for Trench & Field Stop IGBT

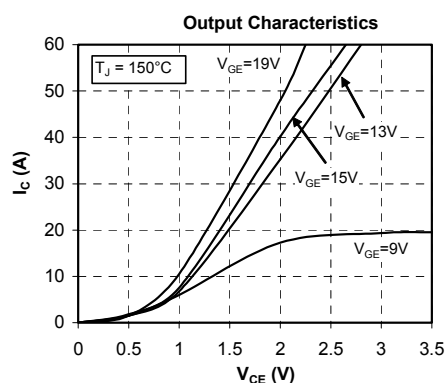
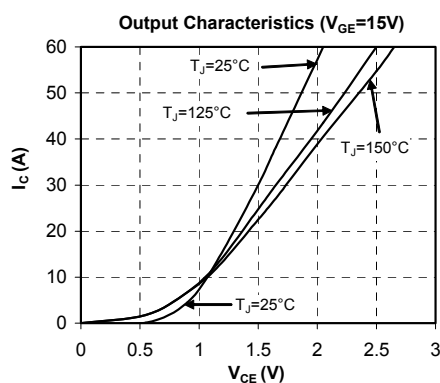
5. SP3 Package outline (dimensions in mm)

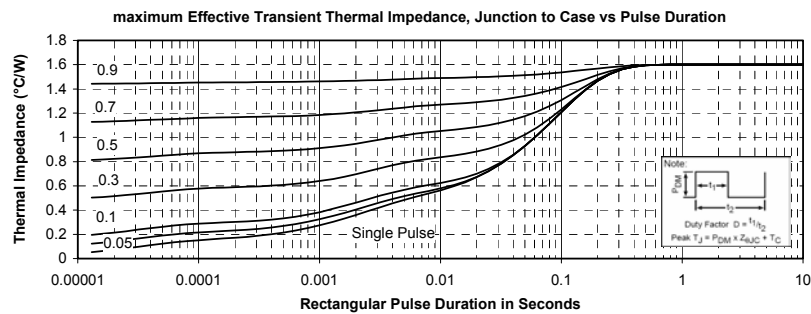
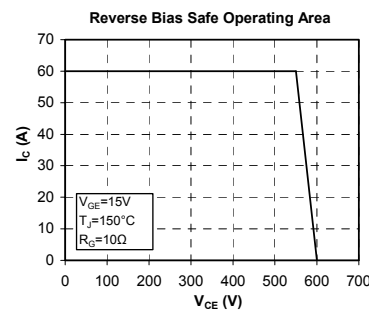
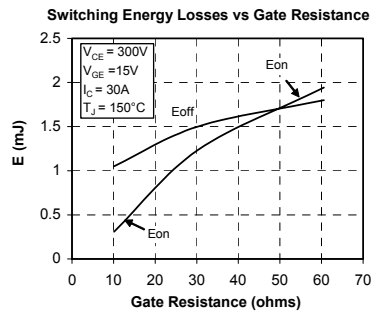
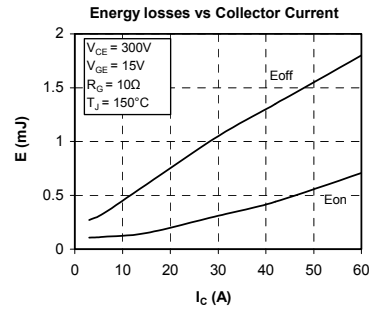
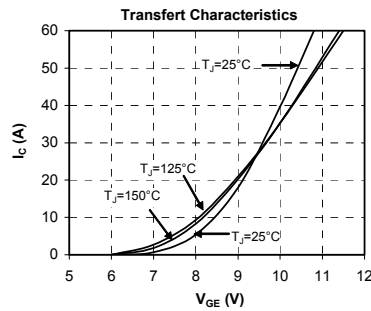


See application note 1901 - Mounting Instructions for SP3 Power Modules on www.microsemi.com

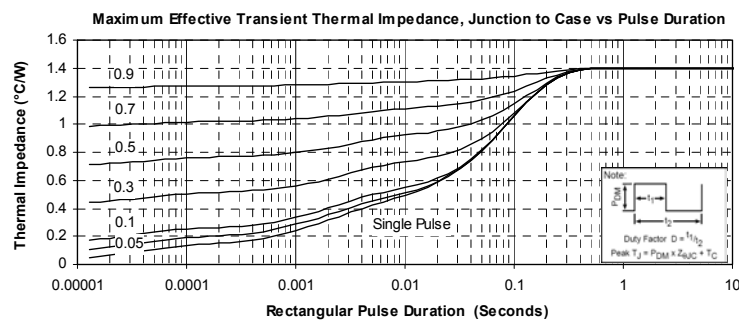
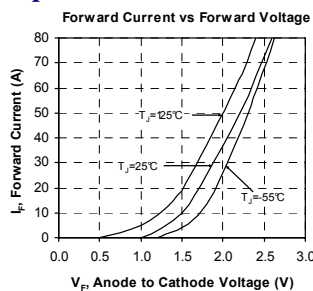
6. Top switches curves

6.1 Top Trench + Field Stop IGBT® typical performance curves



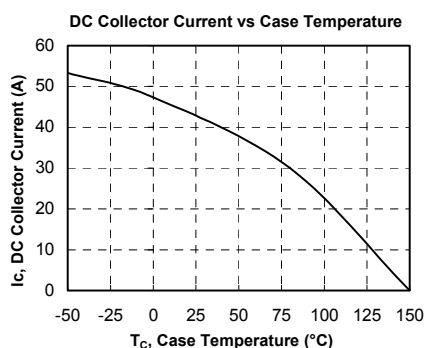
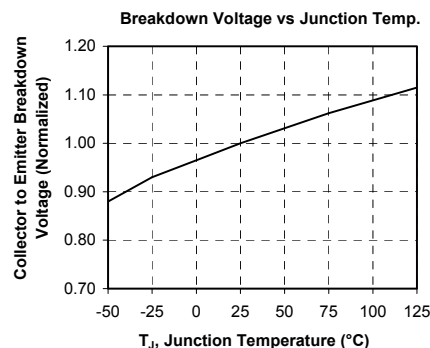
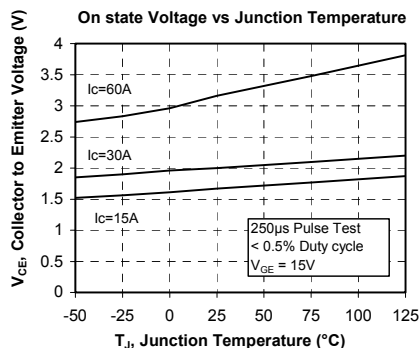
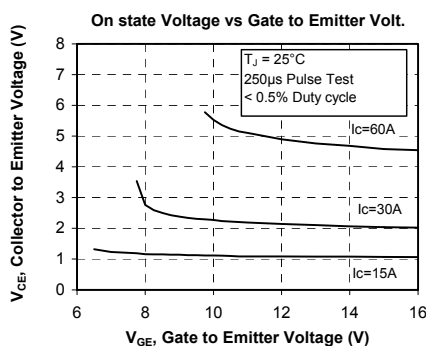
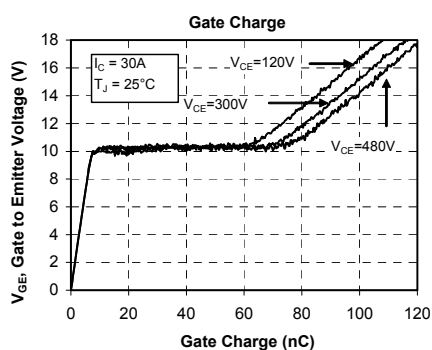
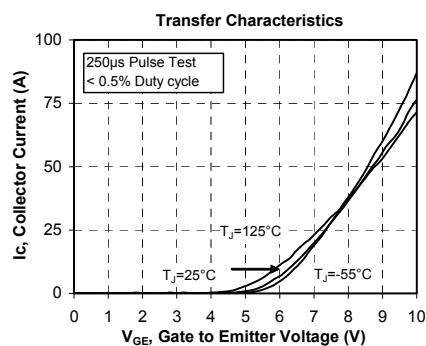
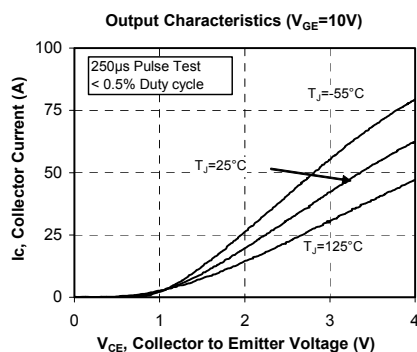
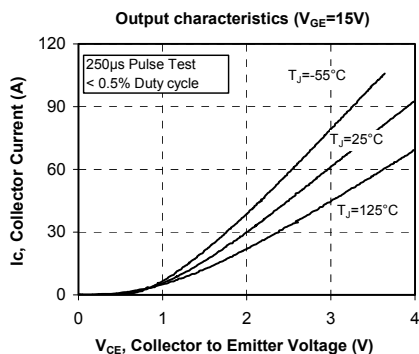


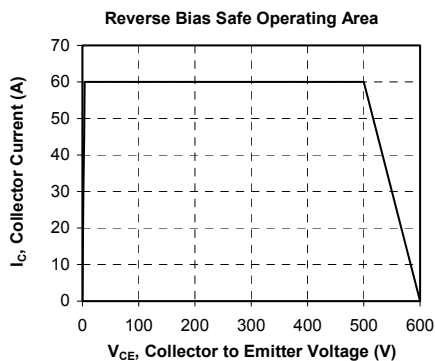
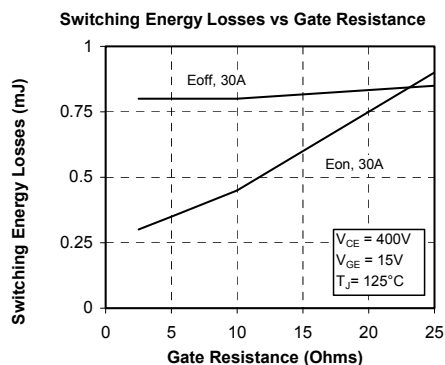
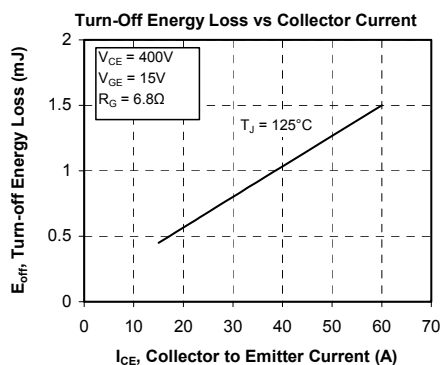
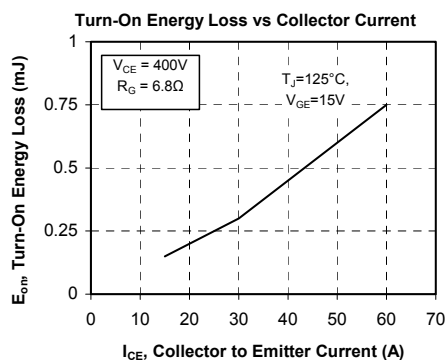
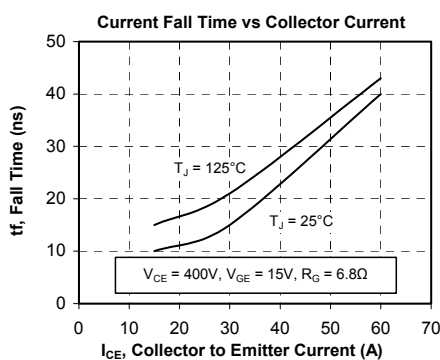
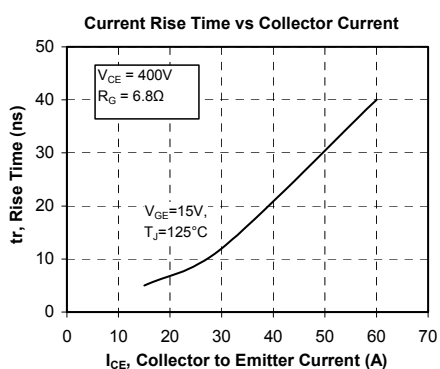
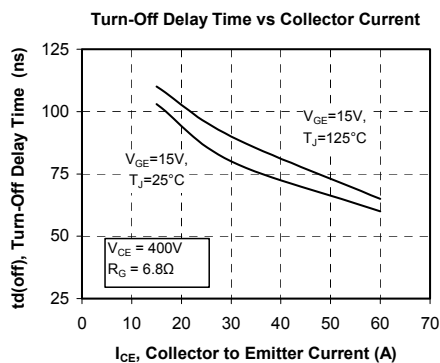
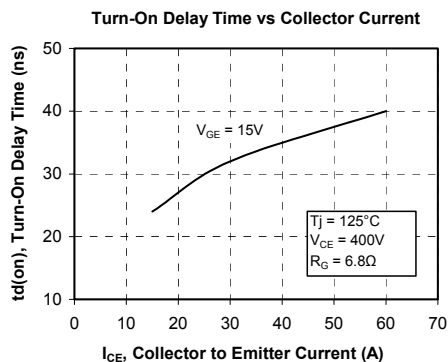
6.2 Top Fast diode typical performance curves

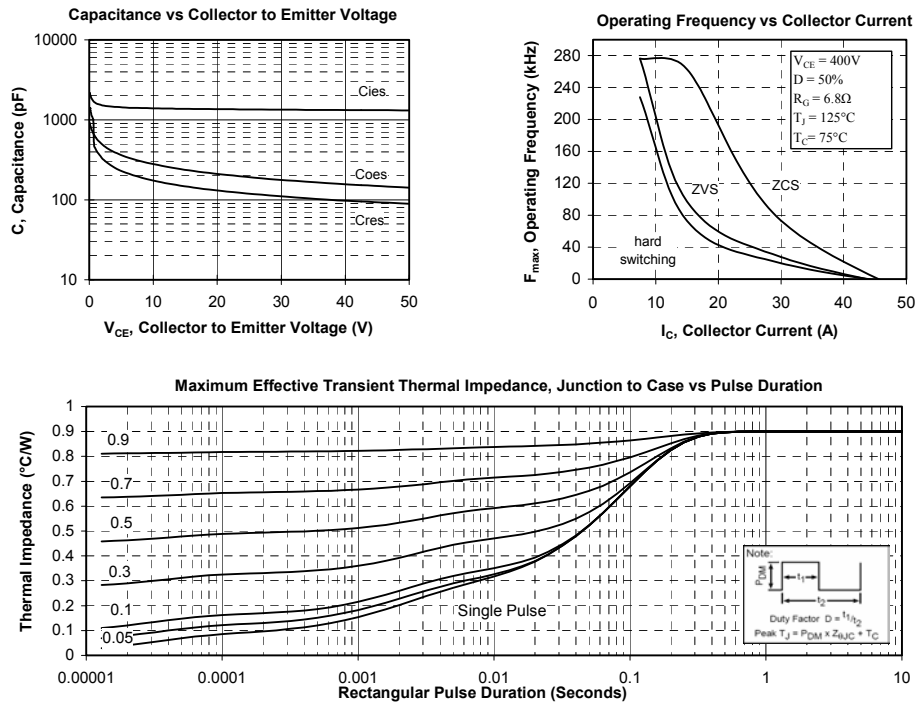


7. Bottom switches curves

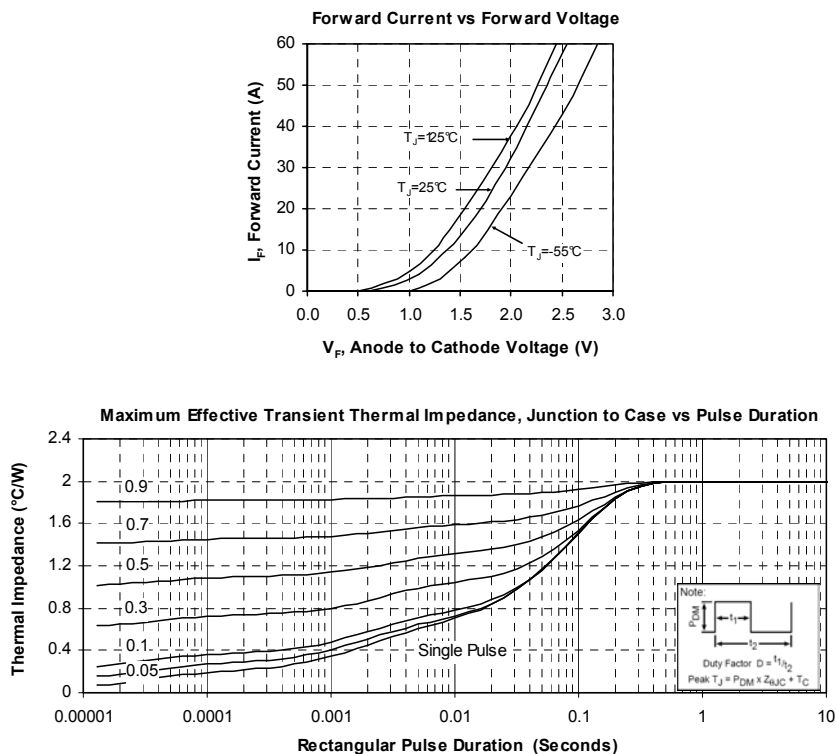
7.1 Bottom fast NPT IGBT typical performance curves







7.2 Bottom diode typical performance curves



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